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# Phase-Field Modeling of Aging of Energetic Thin Films

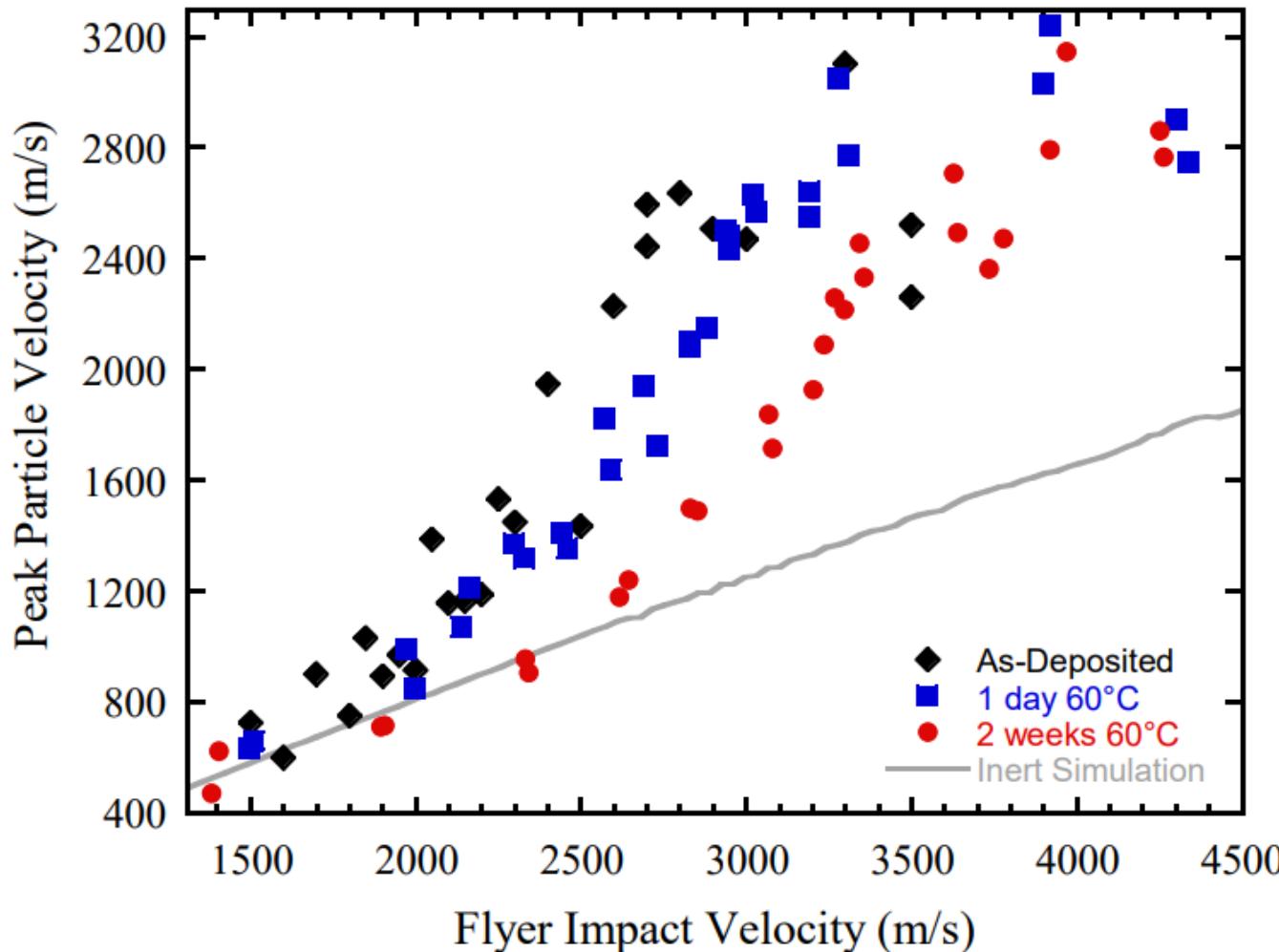
**Joseph Monti**, James Stewart, David Damm,  
Rémi Dingreville

Sandia National Laboratories

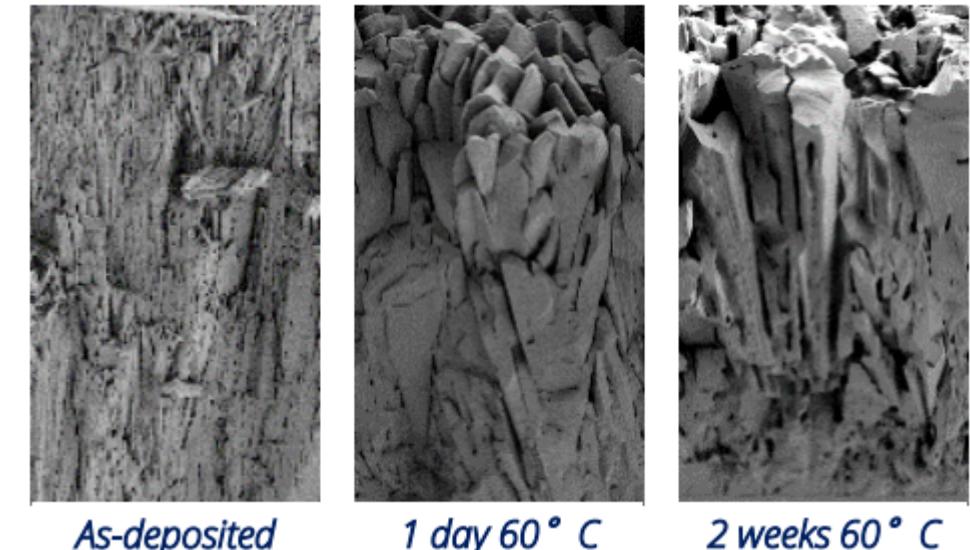
APS SCCM 23

June 19<sup>th</sup>, 2023

# Ageing Effects on Initiation Threshold and Microstructure



PETN thin films



As-deposited

1 day 60 °C

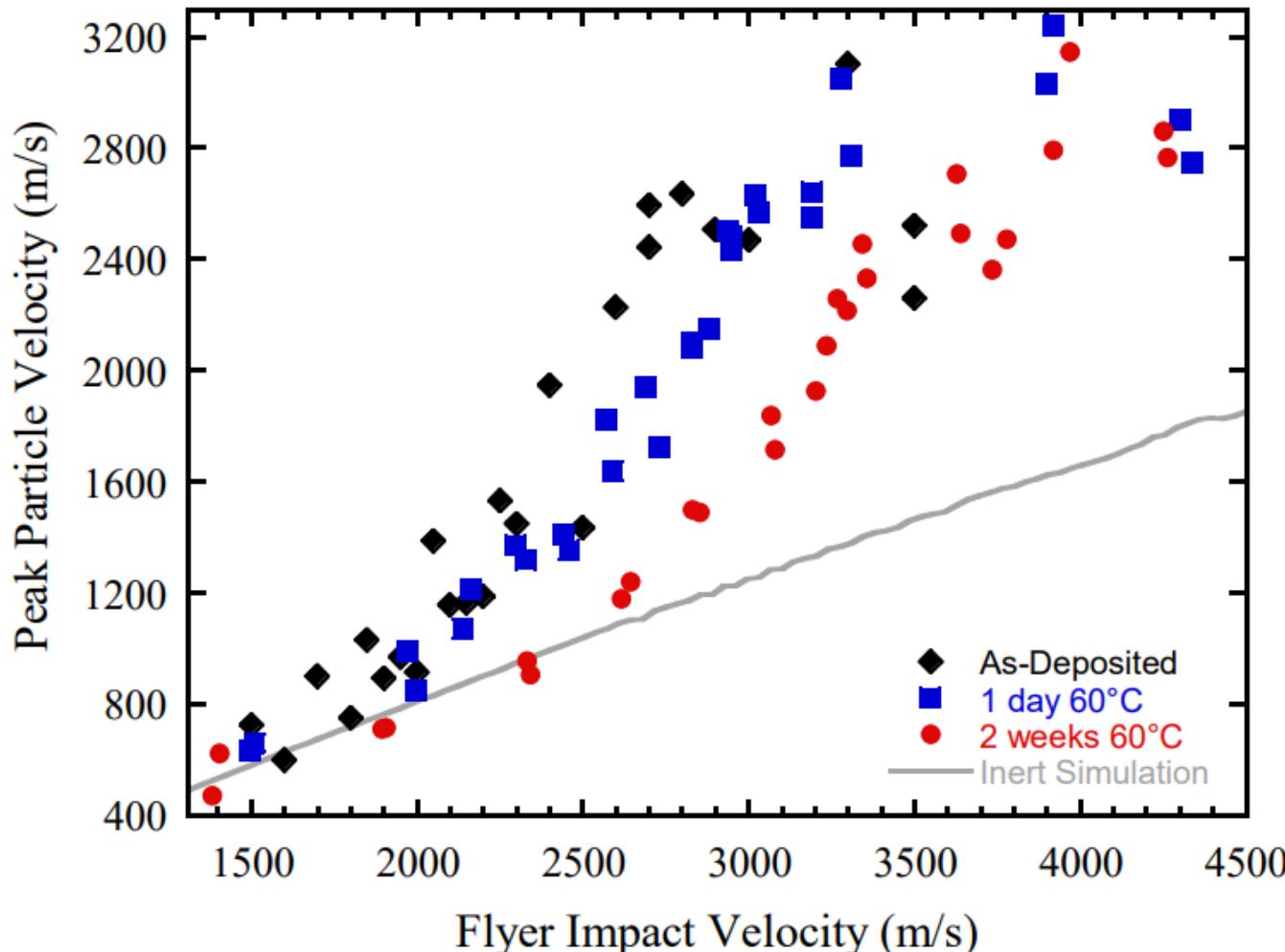
2 weeks 60 °C

Goal is to predict microstructure evolution using Phase-Field modeling

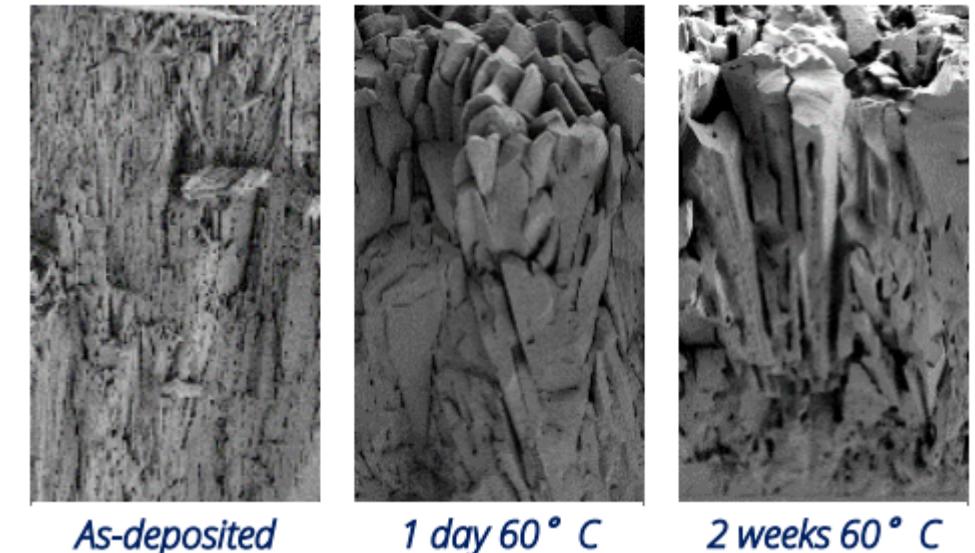
Developing a mesoscale shock initiation model of HTI experiments

Comparison of three distinct stages of ageing in High Throughput Initiation (HTI) data on 100  $\mu\text{m}$  thick samples of PETN

# Ageing Effects on Initiation Threshold and Microstructure



PETN thin films



As-deposited

1 day 60 ° C

2 weeks 60 ° C

Mesoscale shock modeling: F03.00004  
Monday, 4:30-4:45PM by David Damm

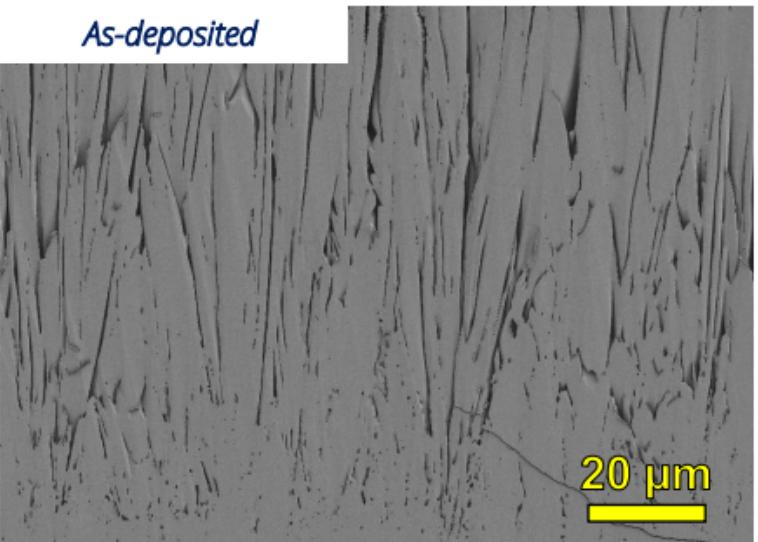
Experimental component: V03.00005  
Thursday, 10:30-10:45AM by Rob Knepper

Comparison of three distinct stages of ageing in High Throughput Initiation (HTI) data on 100  $\mu$ m thick samples of PETN

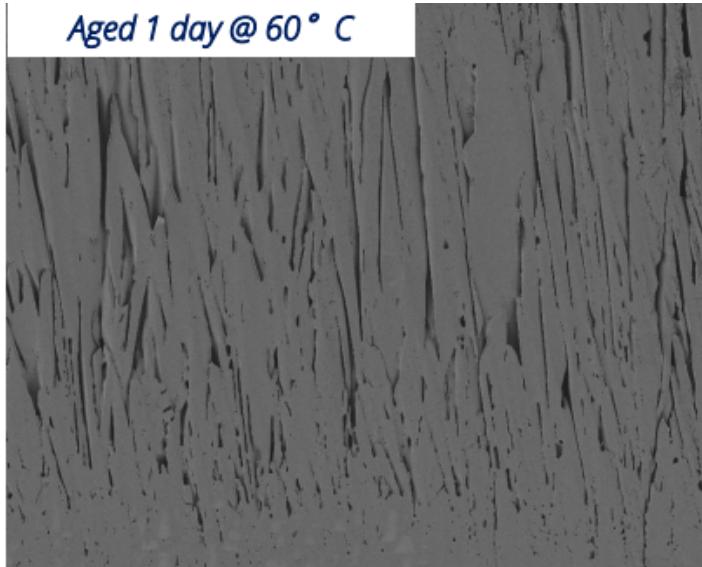
# Microstructural Ageing of PETN films

*SEM images of ion-polished cross-sections in as-deposited and aged PETN films*

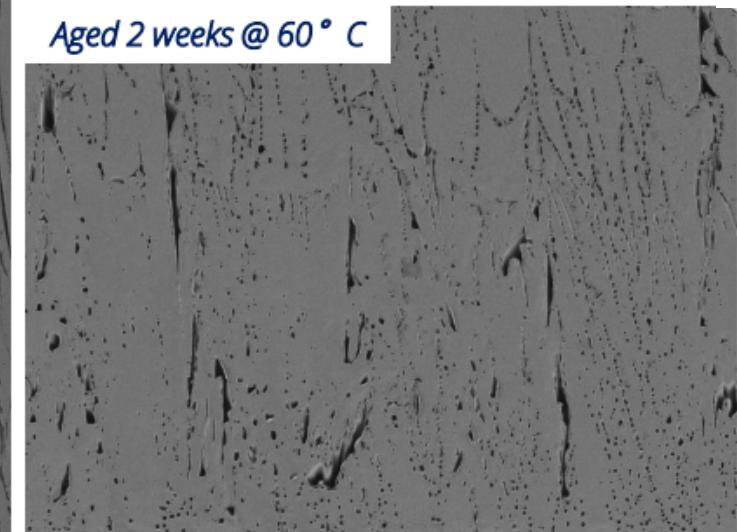
*As-deposited*



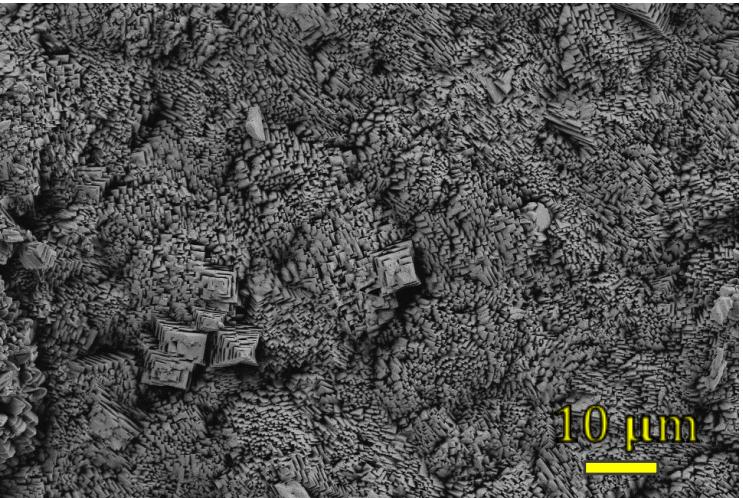
*Aged 1 day @ 60 ° C*



*Aged 2 weeks @ 60 ° C*



*Top surface morphologies*



# Phase-field porous microstructure model

- Model produces coupled evolution of grains and pores
- Key feature: diffuse interfaces between phases

Formulate free-energy functional  $F$ :

$\rho$ : pore-matrix order parameter

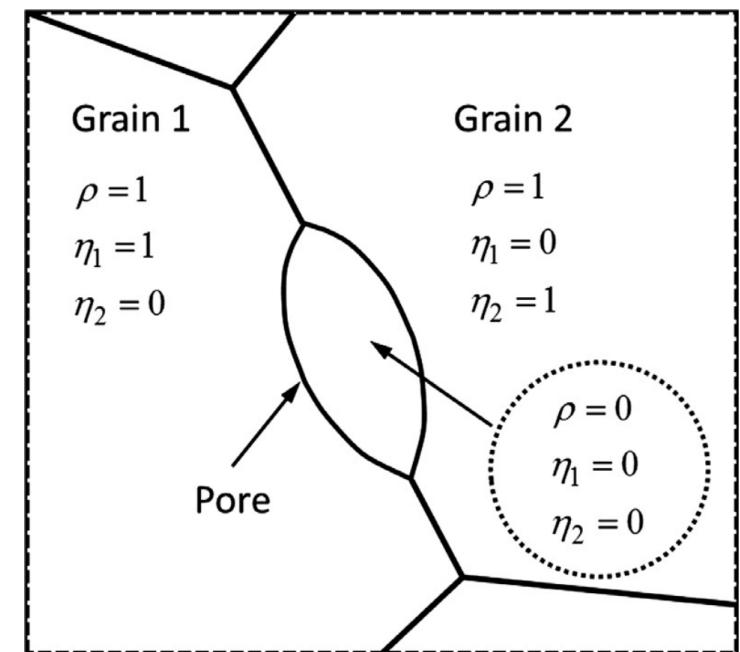
$\vec{\eta}$ : grain order parameters

Allen-Cahn Eqn.  $\rightarrow$  Non-Conserved

$$\frac{\partial \eta_j}{\partial t} = -L_{ij} \frac{\delta F}{\delta \eta_i}$$

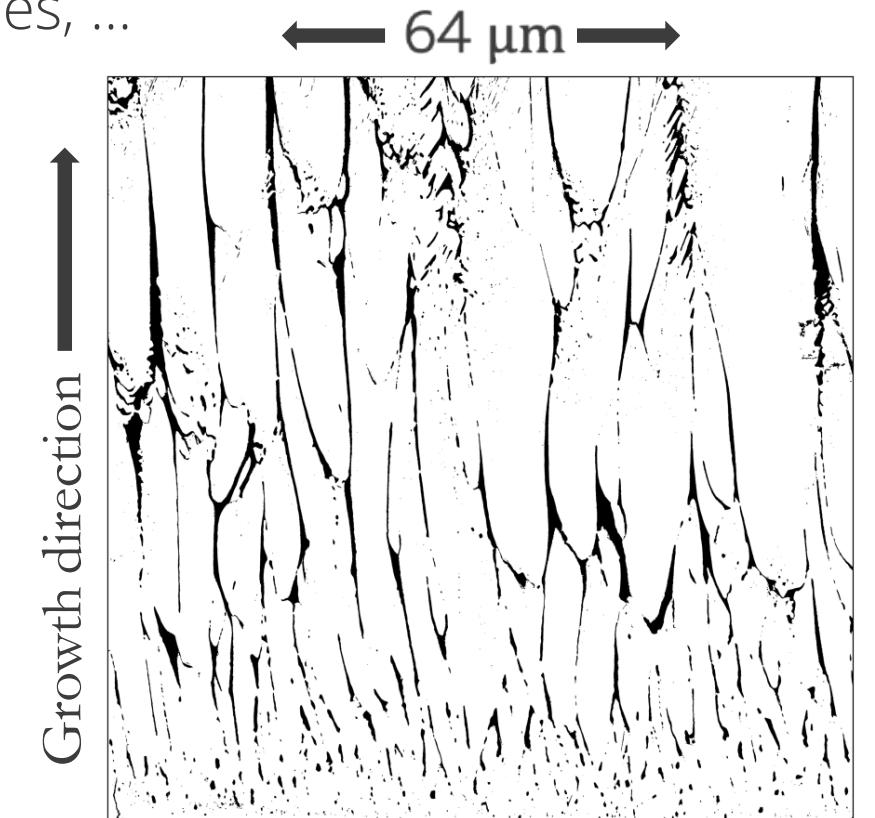
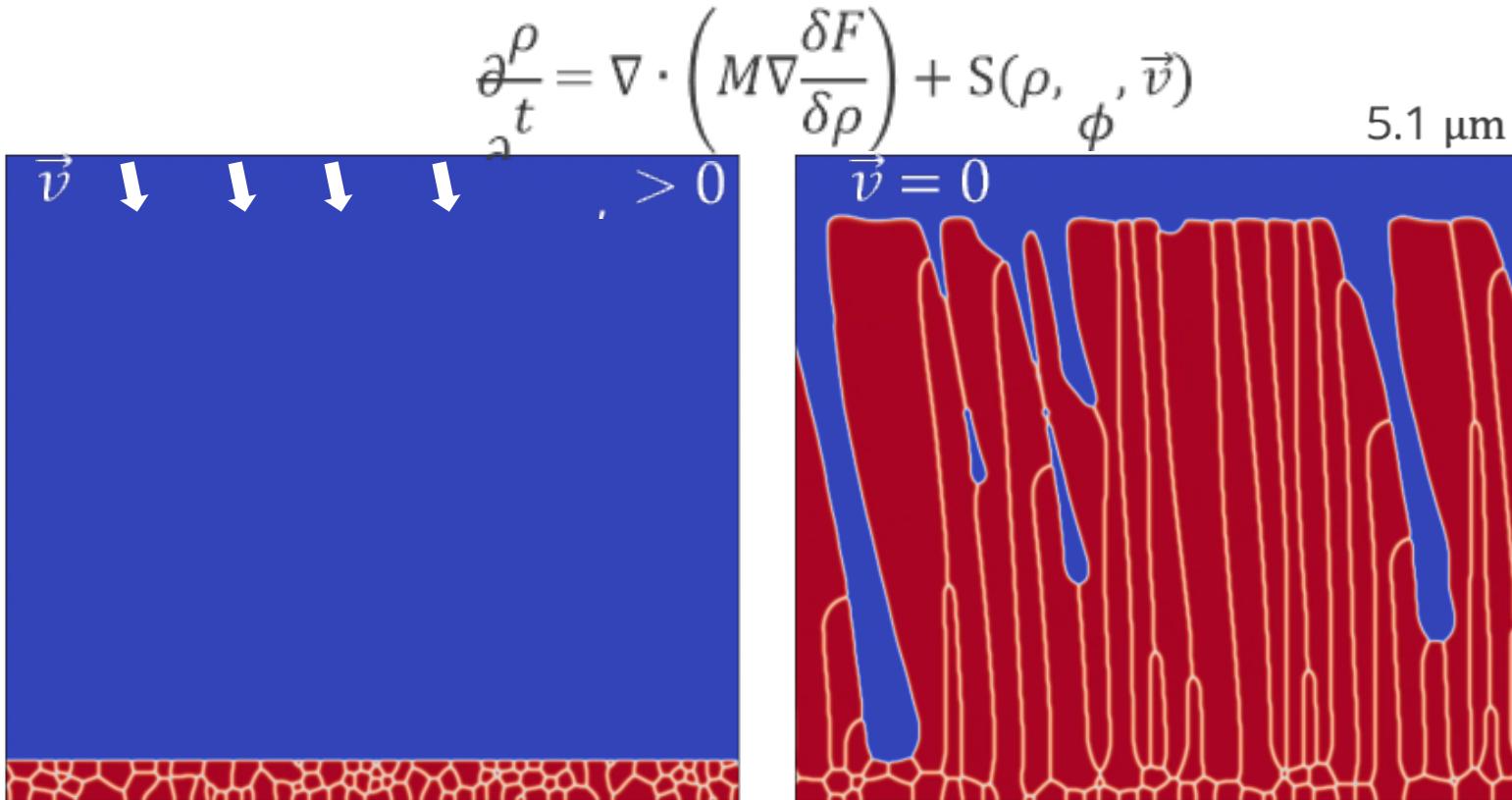
Cahn-Hilliard Eqn.  $\rightarrow$  Conserved

$$\frac{\partial \rho}{\partial t} = \nabla \cdot \left( M \nabla \frac{\delta F}{\delta \rho} \right)$$



# Coupled thin-film growth and porous microstructure evolution models

Film microstructure depends on: chamber pressure,  
deposition incidence angle and rate, substrate properties, ...

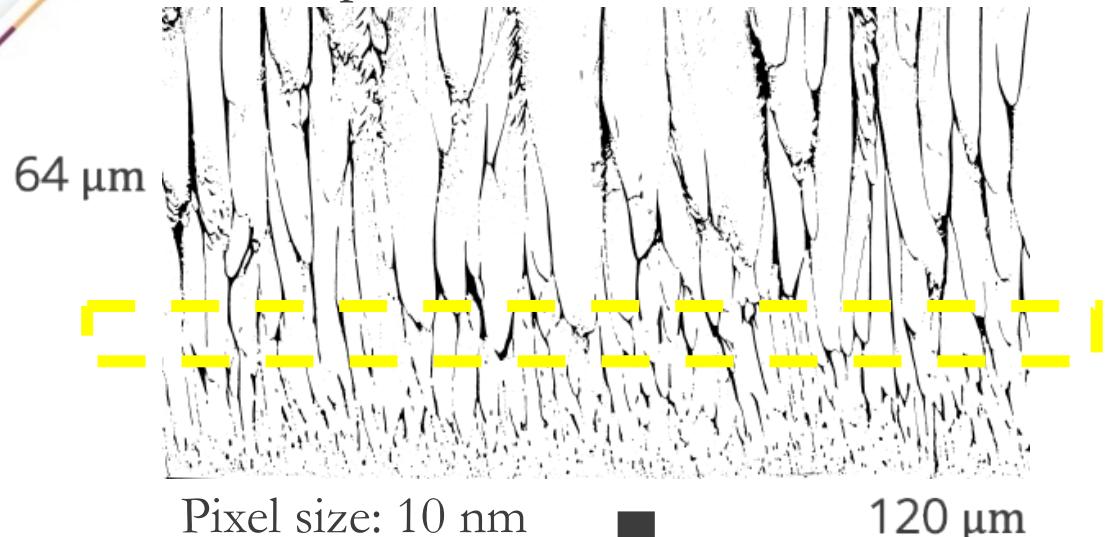


As-deposited PETN cross-section

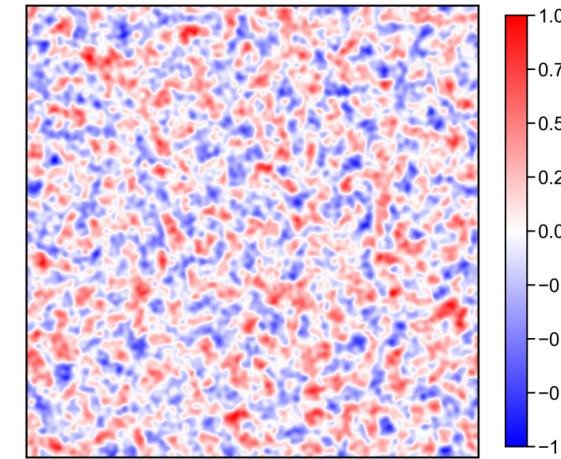
Typical numerical discretization size  $\sim 10$  nm

# Phenomenological model of void trapping during film growth

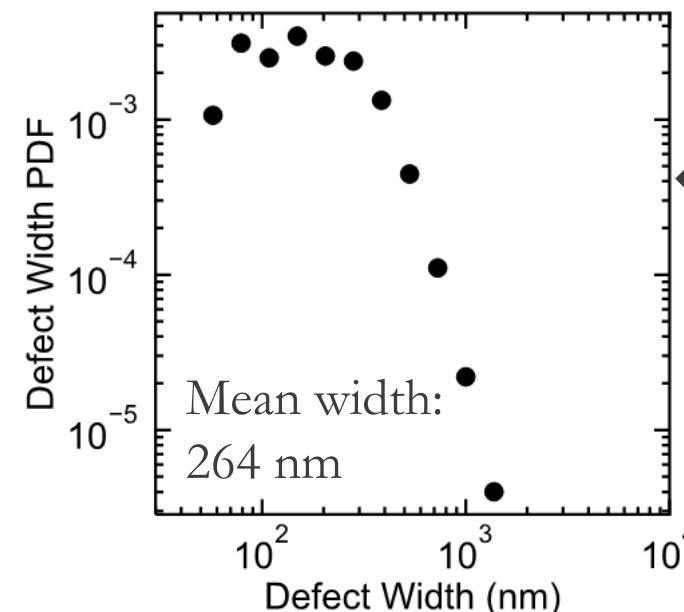
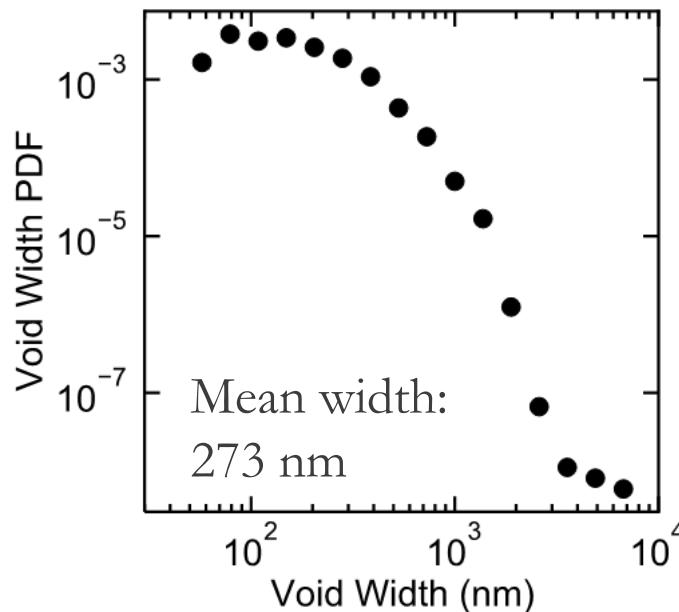
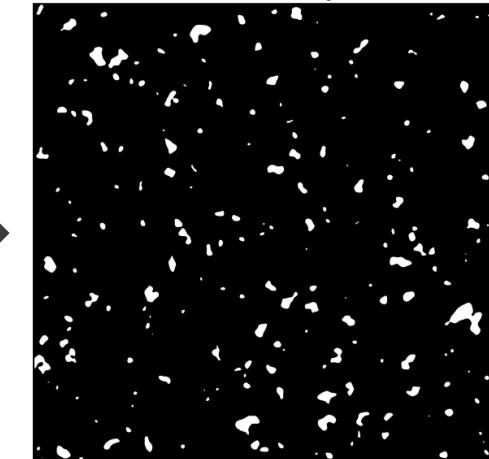
As-deposited PETN cross-section



Gaussian random field



Threshold by value



Defects in vapor deposition:  
Turn off source term locally in  
defect regions as

$$S(\rho, \phi, \vec{v}) = 0$$

# Properties of source field drive vapor-deposited microstructure

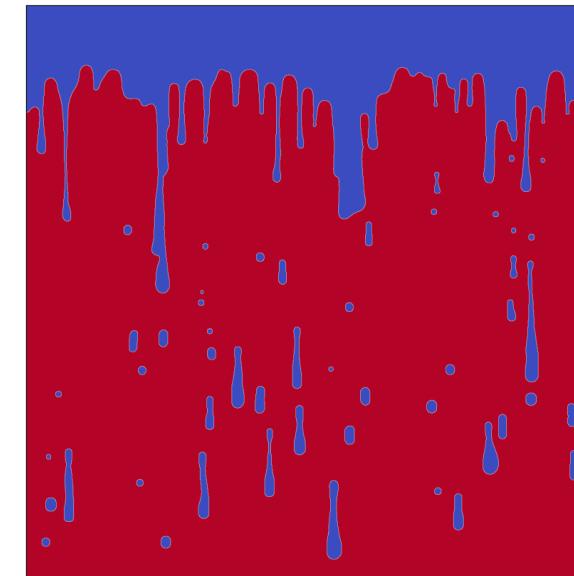
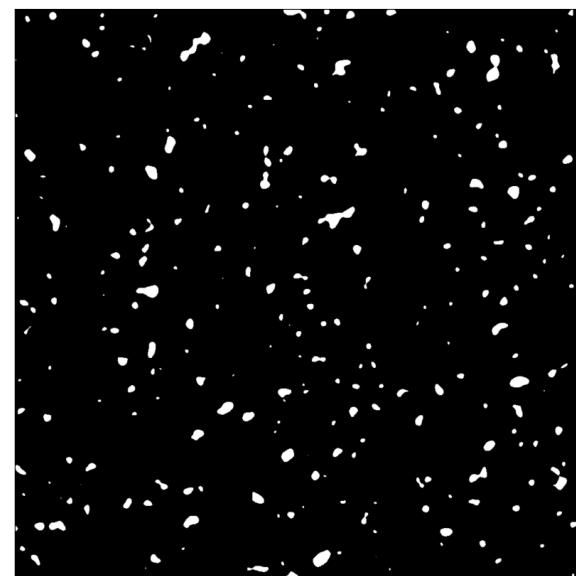
Source defects



Microstructure



Coarse



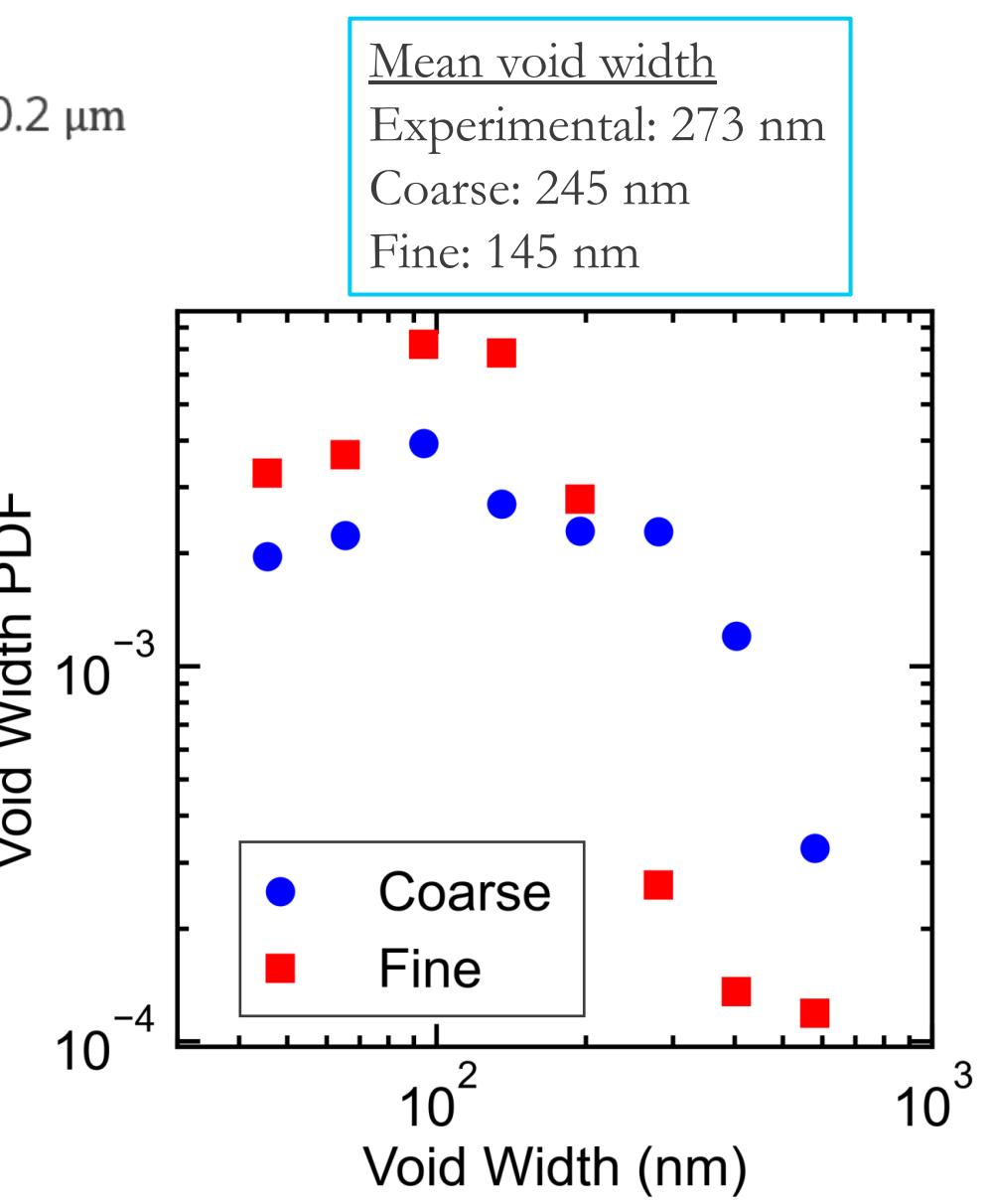
Fine

Mean void width

Experimental: 273 nm  
Coarse: 245 nm  
Fine: 145 nm

10.2 μm

Void Width PDF



## Key phase-field modeling features

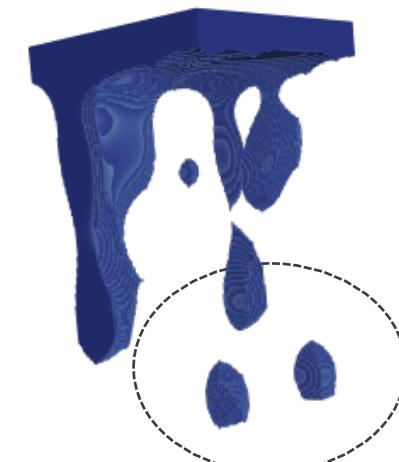
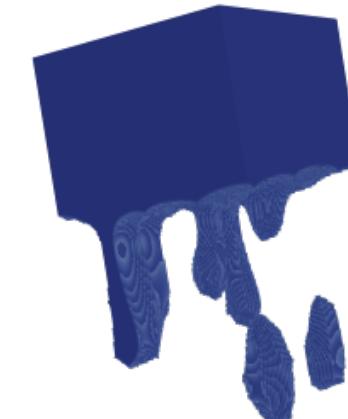
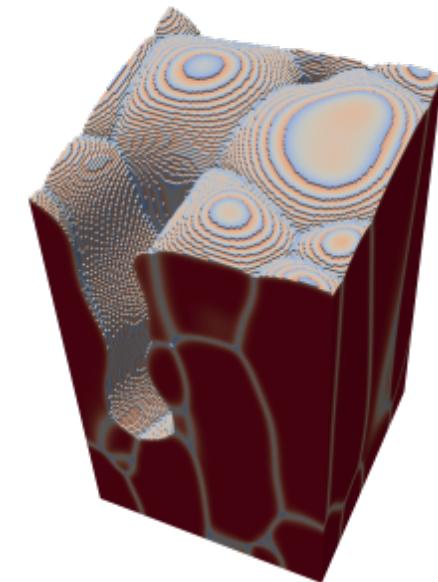
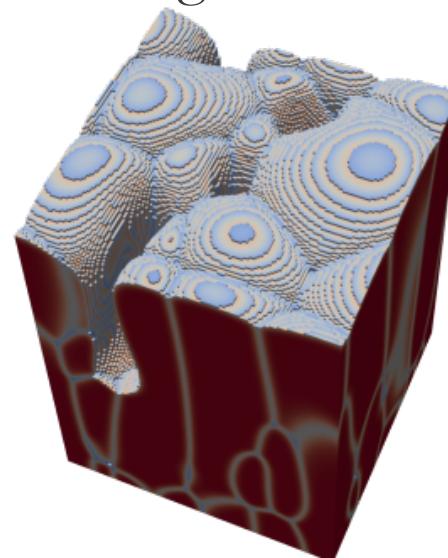
2D and 3D models incorporate concurrent vapor deposition and grain microstructure formation

- Locally inhomogeneous deposition produces **trapped pores** and **elongated voids**
- Source term defect formulation affords control over statistical properties of **porosity distribution**

Output microstructures can be used in subsequent ageing studies, and mesoscale shock initiation simulations

- Ageing following deposition shows **grain growth**, **surface smoothing**, and **void consolidation**

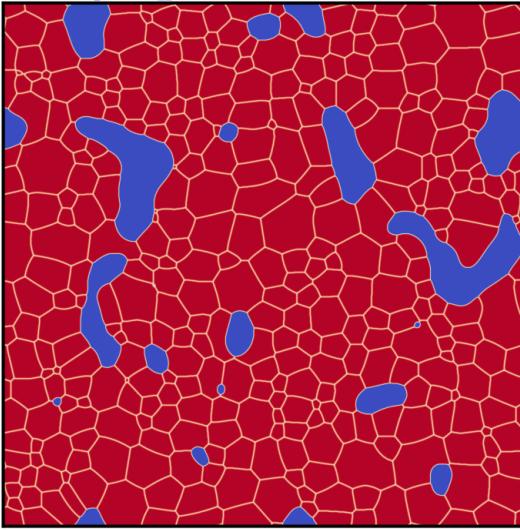
Rough surface topography formation



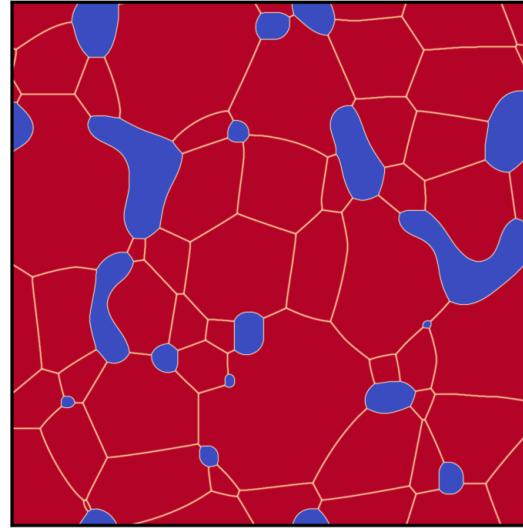
Trapped voids

# Pore size dictates grain growth kinetics

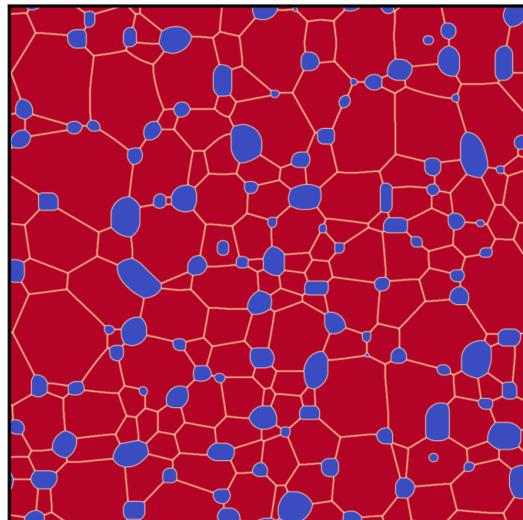
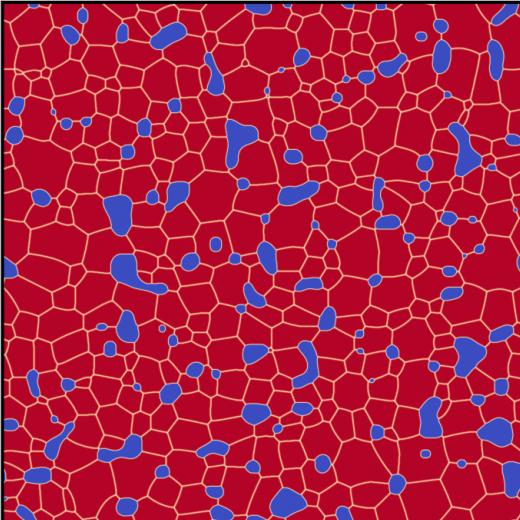
Large pore structure



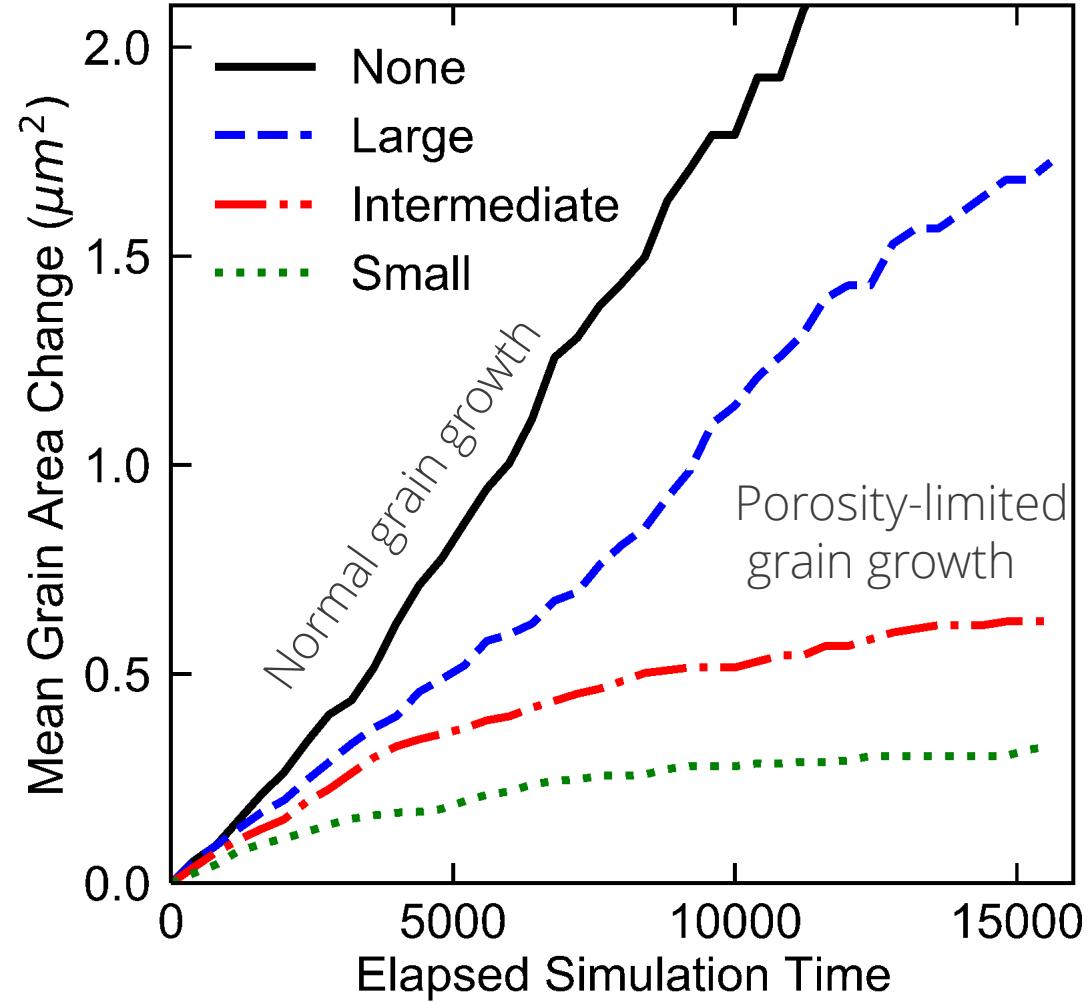
10.2  $\mu\text{m}$



Small pore structure

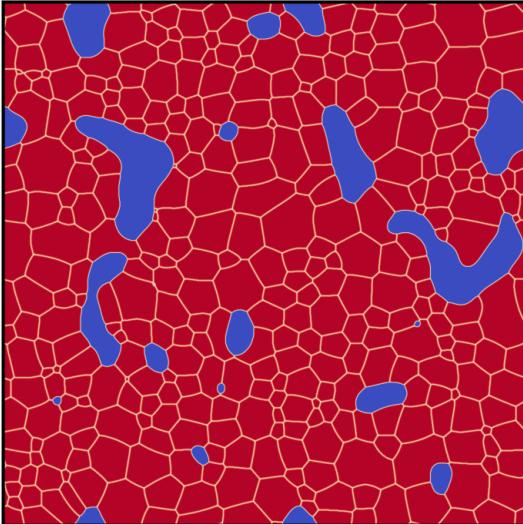


Overall porosity  $\sim 12\%$

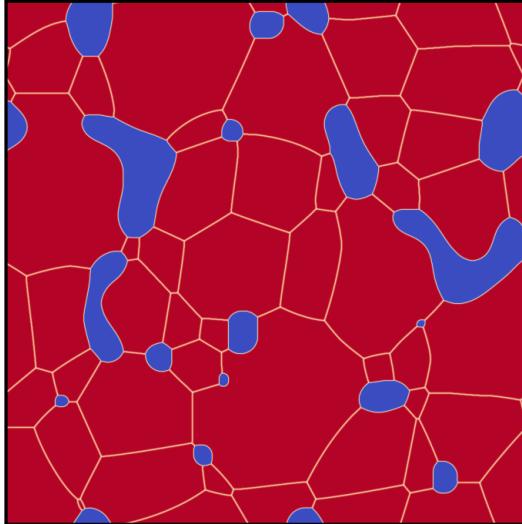


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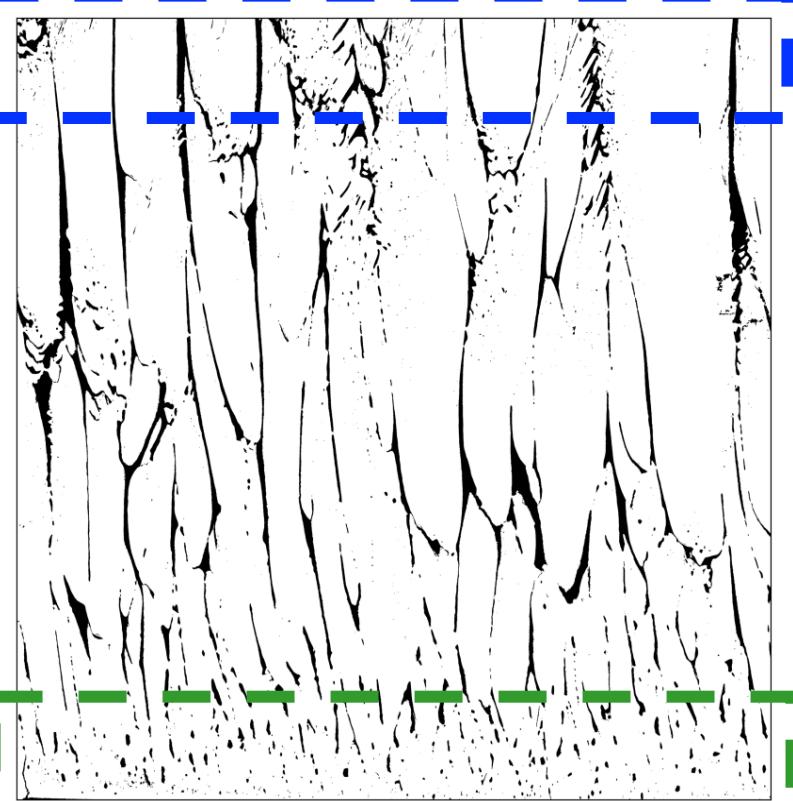
Large pore structure



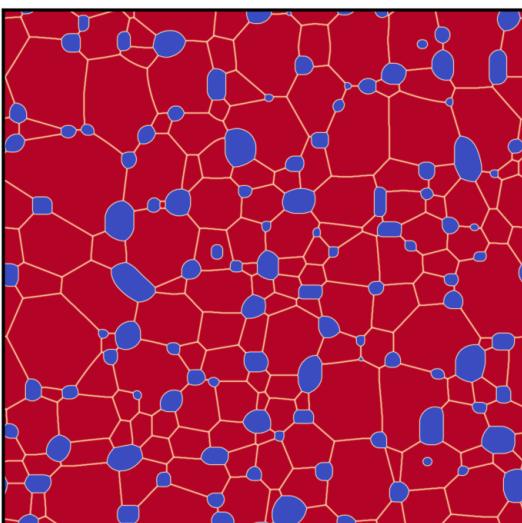
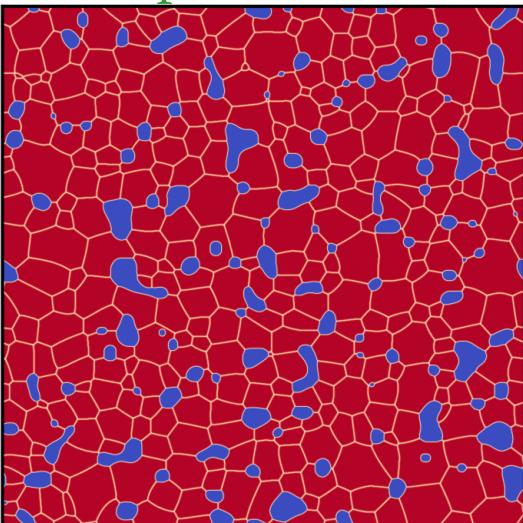
10.2  $\mu\text{m}$



Overall porosity  $\sim 12\%$



Small pore structure



As-deposited PETN cross-section

# Summary

- A coupled porous solid and grain growth phase-field model was augmented to study vapor-deposited energetic thin films with explicit vapor transport
- Defects in vapor deposition flux permitted formation of porosity distributions that qualitatively agree with experimental observations
- Simulations showed abundant, fine porosity limits grain growth more than rare, coarse porosity

